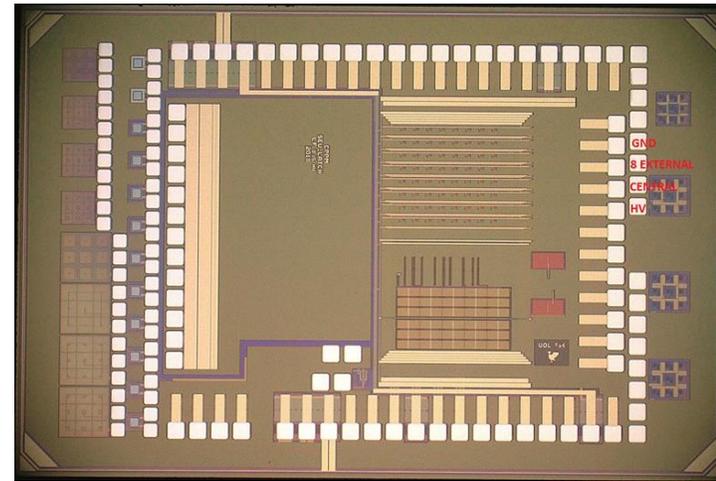
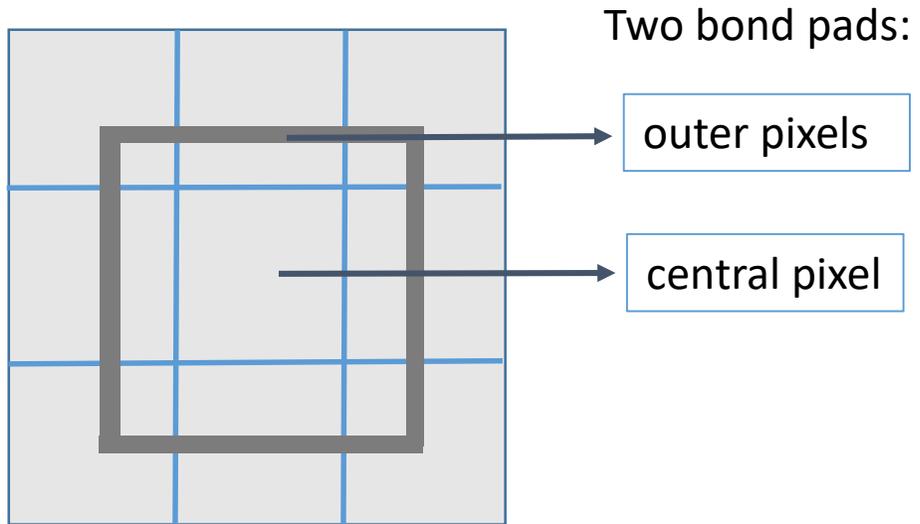


RD50 MPW2 Test structure

- 60 μm x 60 μm pixel
- 3x3 pixel array
- central pixel one bond pad
- outer pixels connected together another bond pad



In our setup:

DNWELL connected to
+ HV

Substrate (HV)
to GND

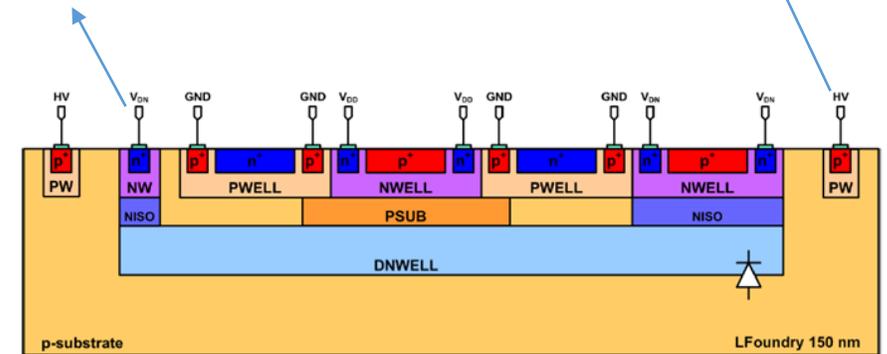
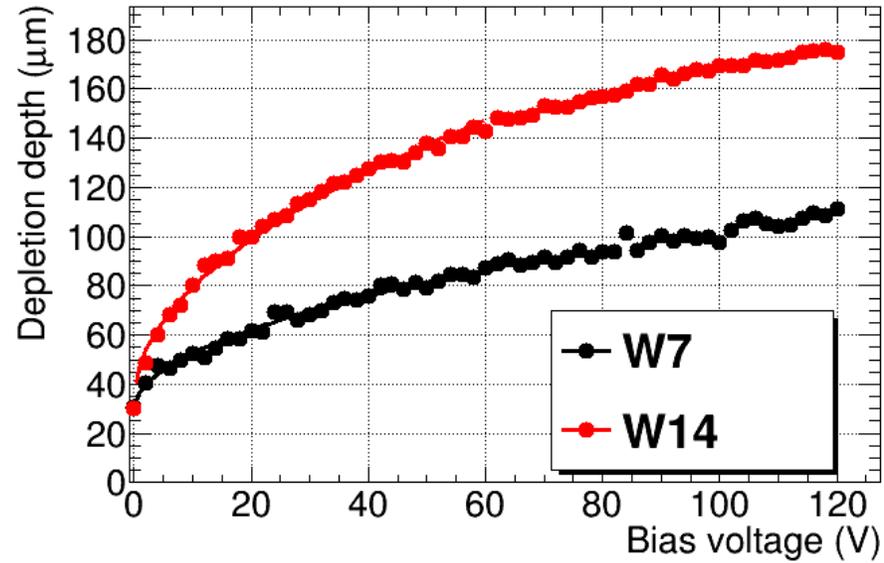
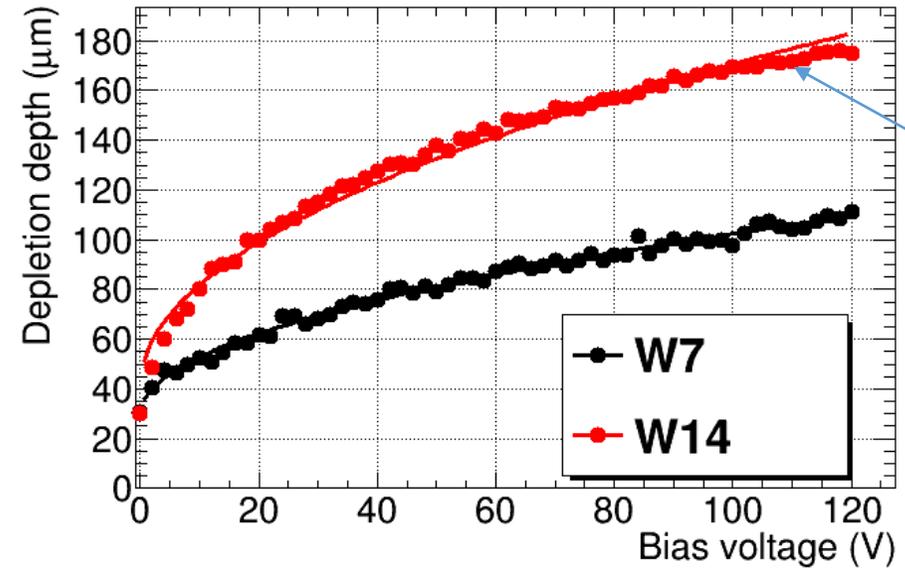


Figure 12. Simplified cross-section of one pixel

Fit up to 60 V



Fit up to 120 V



slabši fit
kot do 60 V

Fit:

$$d = d_0 + \sqrt{\frac{2\epsilon\epsilon_0}{e_0 N_{eff}} \cdot V_{sub}}$$

Fit up to 60 V:

Neff_w7 = 2.4e13

Neff_w14 = 6e12

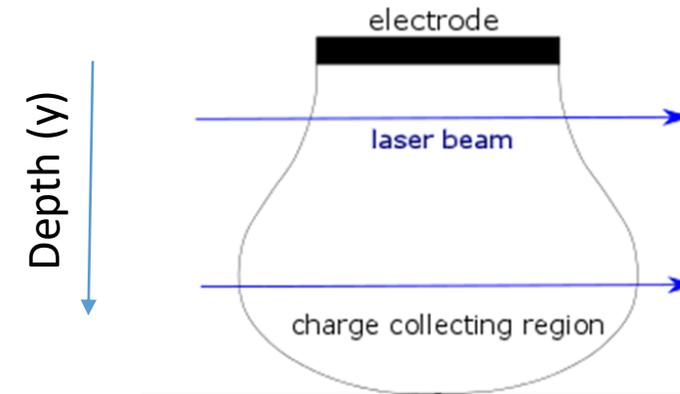
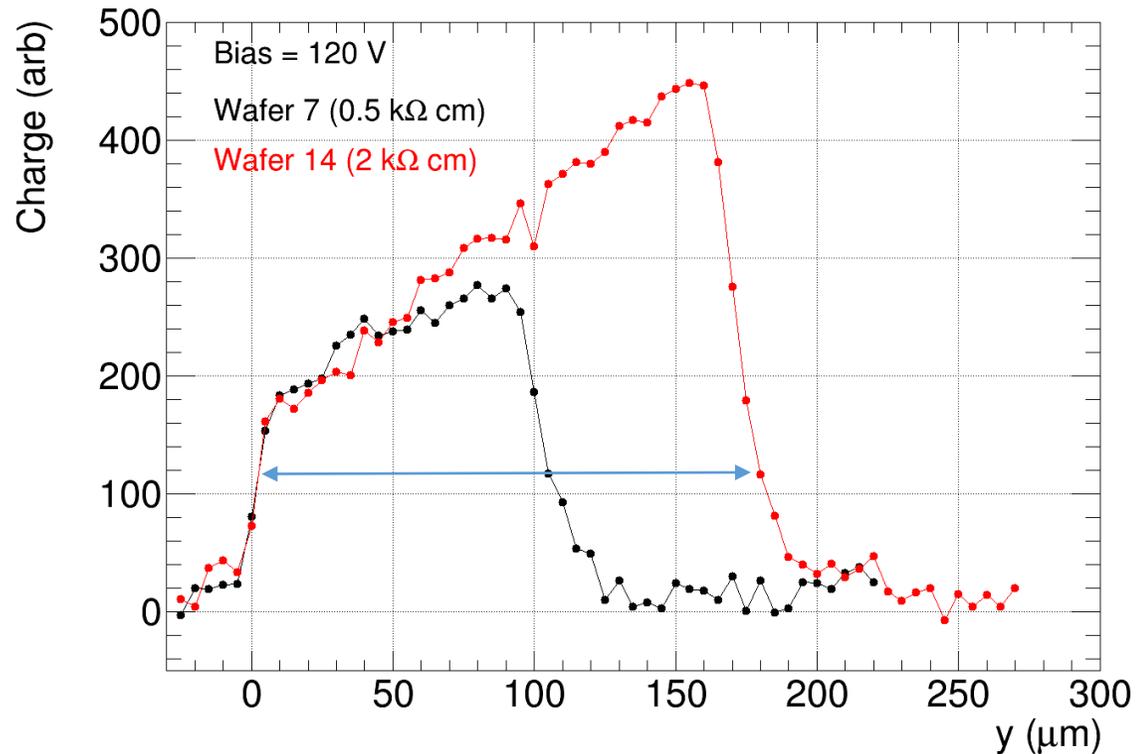
Fit up to 120 V:

Neff_w7 = 2.5e13

Neff_w14 = 8e12

Pri w14 precejšnja razlika če fit do 60 V ali do 120 V

Charge collection profile



- more charge collected at larger y (depth) because length of laser beam inside charge collection region increases because of the shape of the region

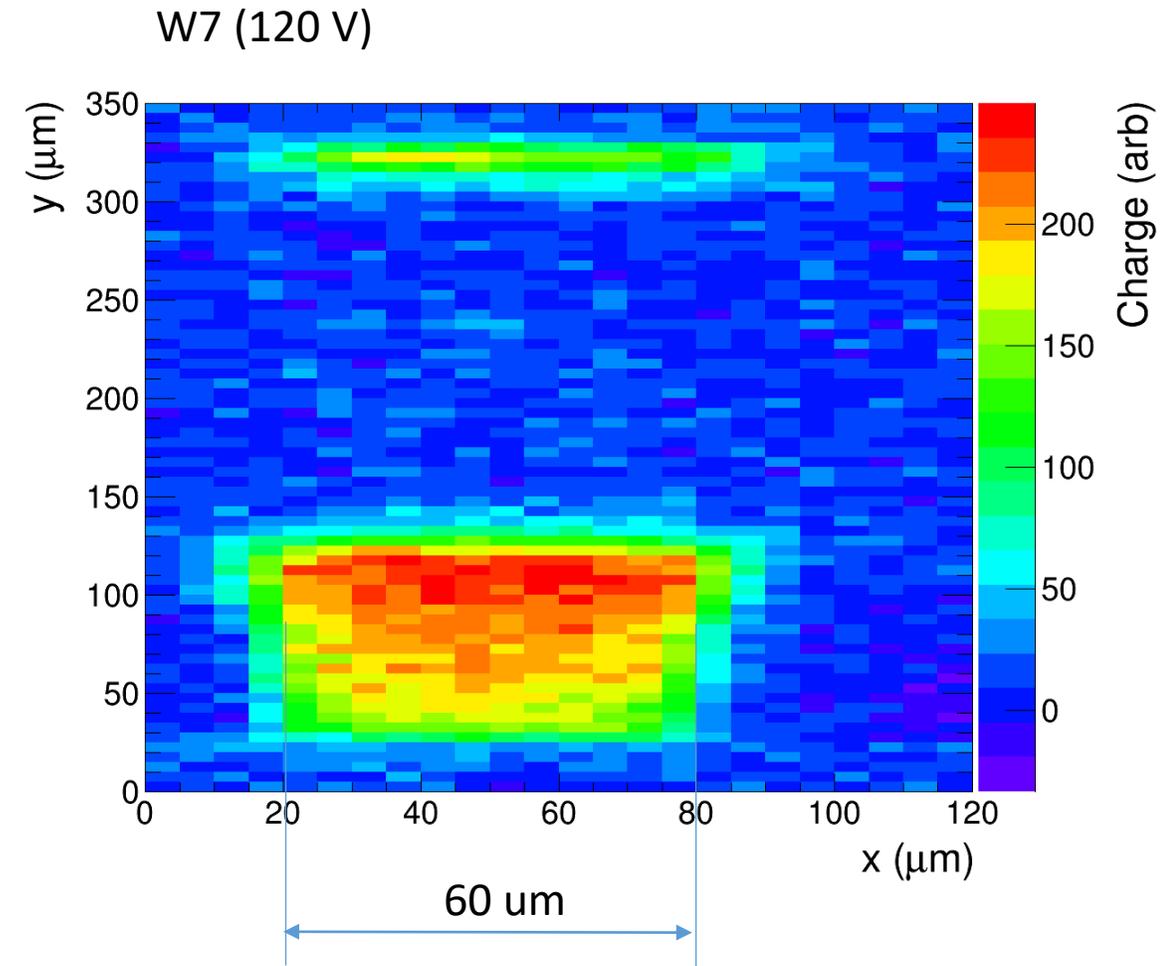
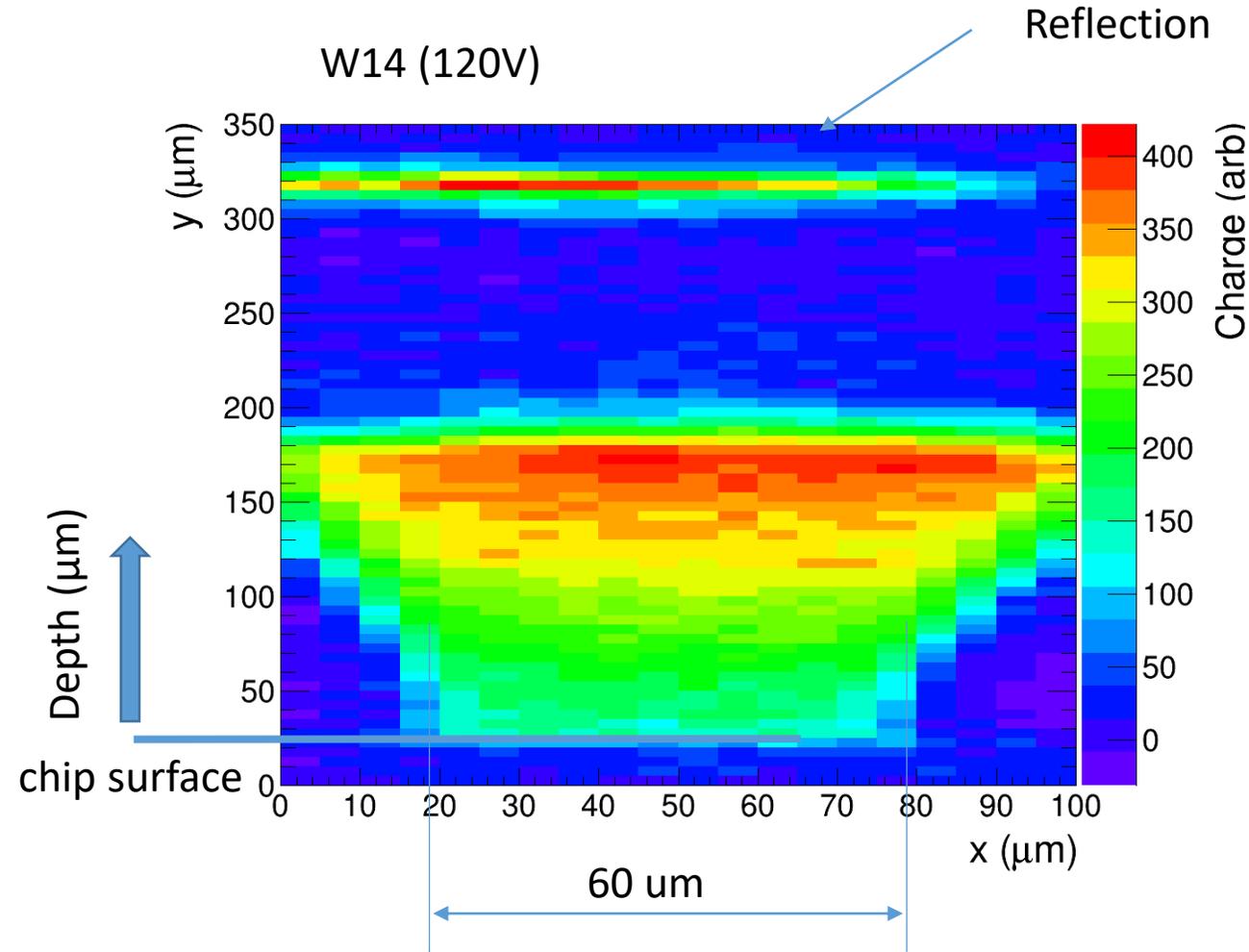
Čudna oblika depletiranega območja

➔ Kako dobro enačba opiše odvisnost d od V in N_{eff} ?

➔ Bi se dalo to študirati za magisterij npr. s KDetSim ?

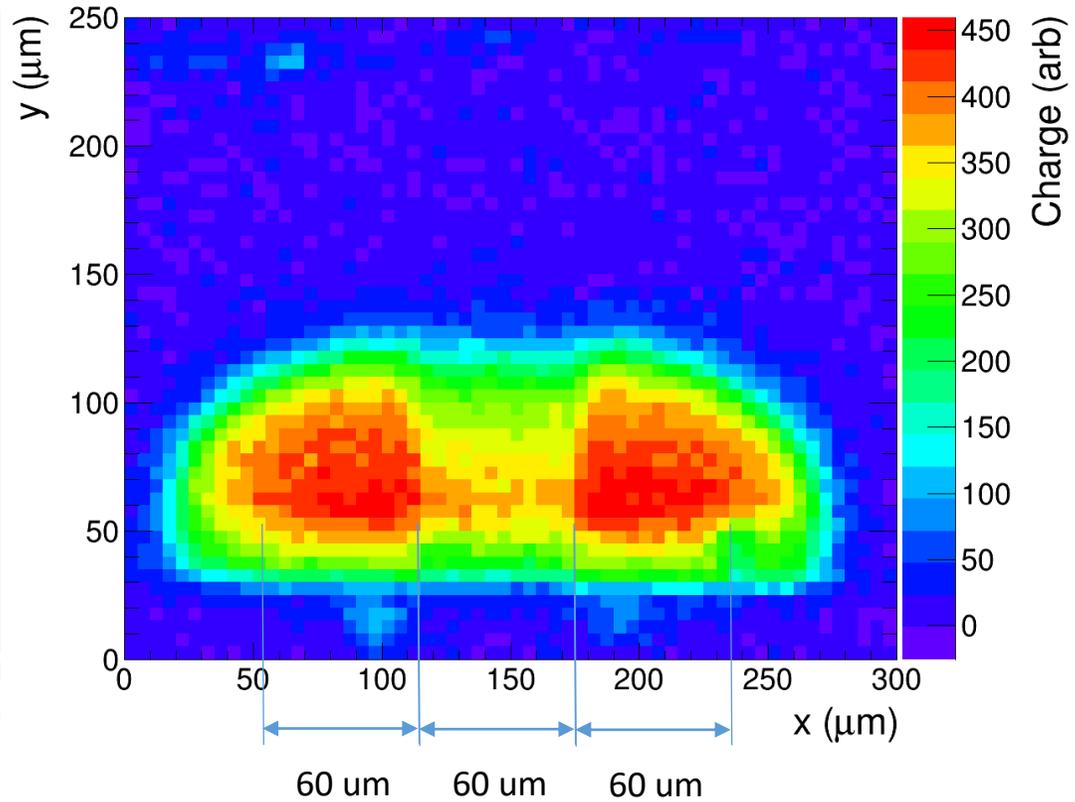
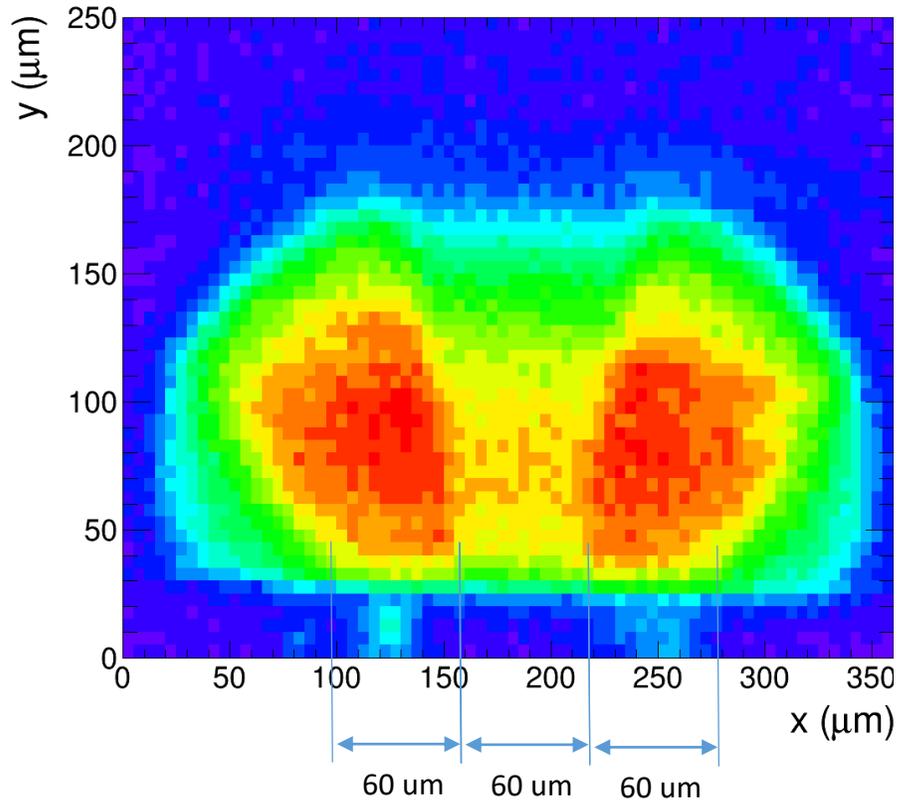
$$d = d_0 + \sqrt{\frac{2\varepsilon\varepsilon_0}{e_0 N_{eff}} \cdot V_{sub}}$$

Scan x and y under central pixel

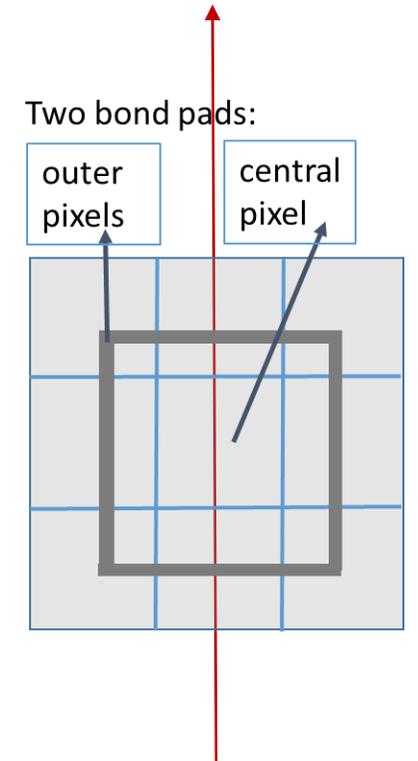


- charge collection region width increases at large depletion depths
- Known effects, seen before in several other samples

Charge from induced signals on outer 8 pixels (without central one)



Top view:

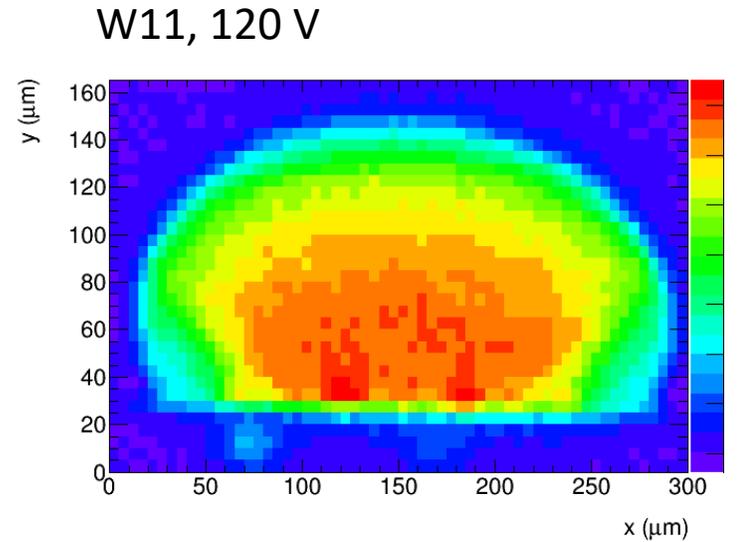
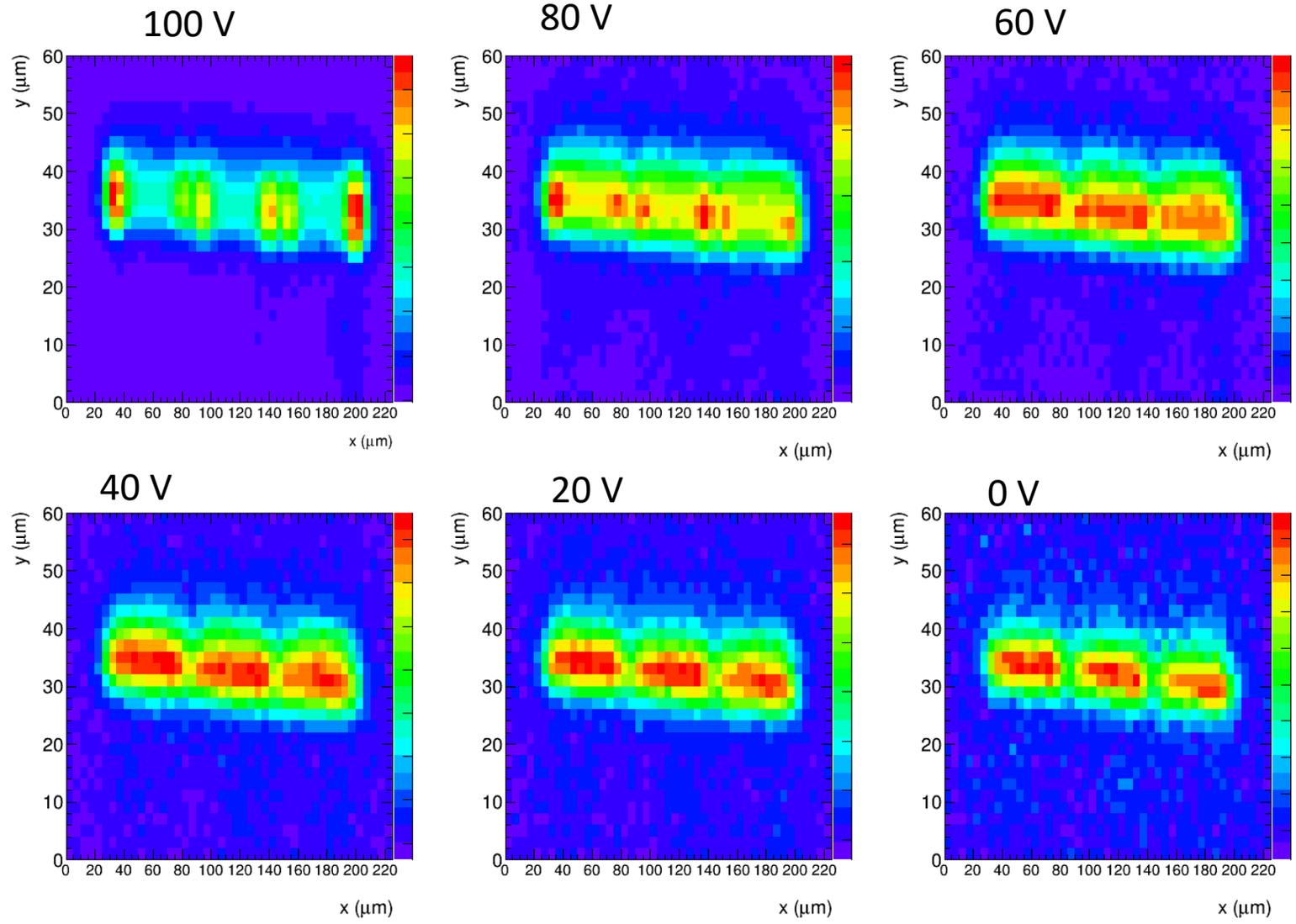


IR laser direction in E-TCT

Charge from central pixel not included

Charge collection region extends beyond dimension of the test structure
→ depletion region shape and diffusion from undepleted substrate

Charge collection profiles



No structure in x direction
For higher resistivities

- W5: → at high bias voltage more charge near pixel edges
- at lower bias gaps between pixels → looks like not depleted
- would be interesting to compare to simulations